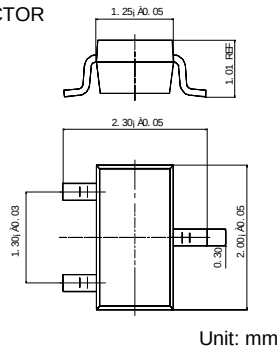
2SC4097 TRANSISTOR(NPN)

SOT-323



1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

FEATURES

Power dissipation

P_{CM}: 200 mW (Tamb=25℃)

Collector current

I_{CM}: 500 mA

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=20V, I_E=0			1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V, I_C=0			1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=3V, I_C=10mA	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA, I_B=10mA			0.4	V
Transition frequency	f_T	V_{CE}=5V, I_C=20mA, f=100MHz		250		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		6		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	**P**	**Q**	**R**
Range	82-180	120-270	180-390
Marking	**CP**	**CQ**	**CR**

WEJ ELECTRONIC CO.